TECHNICAL DATA DATA SHEET 5575, REV -

# HERMETIC POWER MOSFET N-CHANNEL

### **FEATURES:**

- 500 Volt, 0.4 Ohm, 12.0A MOSFET
- Low R<sub>DS (on)</sub>
- Equivalent to IRF450 Series

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## **MAXIMUM RATINGS**

ALL RATINGS ARE AT  $\rm T_{\rm C}$  = 25°C UNLESS OTHERWISE SPECIFIED.

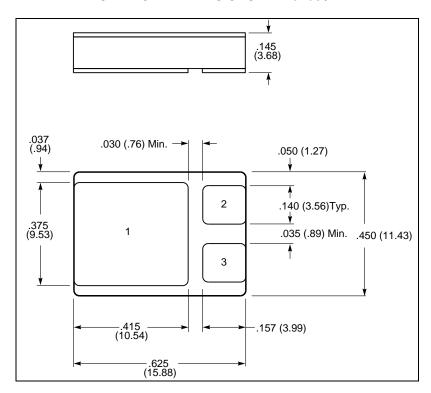
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V <sub>GS</sub>	-	-	±20	Volts
ON-STATE DRAIN CURRENT @ $T_C = 25^{\circ}C$	ΙD	-	-	12	Amps
ON-STATE DRAIN CURRENT @ $T_C = 100^{\circ}$ C	i I <sub>D</sub>	-	-	7.75	Amps
OPERATING AND STORAGE TEMPERATURE	T <sub>OP</sub> /T <sub>STG</sub>	-55	-	+150	°C
TOTAL DEVICE DISSIPATION @ T <sub>C</sub> = 25°C	P <sub>D</sub>	-	-	150	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{thJC}$	-	-	0.83	°C/W

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV <sub>DSS</sub>	500			Volts
$V_{GS} = 0V, I_{D} = 1.0mA$			-	-	
STATIC DRAIN TO SOURCE ON STATE RESISTANCE					
$V_{GS} = 10V, I_{D} = 7.75A$	R <sub>DS(ON)</sub>	-	-	0.43	Ω
$V_{GS} = 10V, I_D = 12A$		-	0.50	-	
GATE THRESHOLD VOLTAGE V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 0.25mA	V <sub>GS(th)</sub>	2.0	-	4.0	Volts
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = Max. Rating, V_{GS} = 0V$	I <sub>DSS</sub>	-	-	25	μΑ
$V_{DS} = Max. Rating, V_{GS} = 0V, T_J = 125^{\circ}C$	250				
GATE TO SOURCE LEAKAGE FORWARD V <sub>GS</sub> = 20V	Igss	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE V <sub>GS</sub> = -20V				-100	
TURN ON DELAY TIME $V_{DD} = 250V$ ,	t <sub>d(ON)</sub>		35	50	
RISE TIME $I_D = 12A$ ,	t <sub>r</sub>	_	190	240	nsec
TURN OFF DELAY TIME $R_G = 2.35\Omega$	t <sub>d(OFF)</sub>		170	220	
FALL TIME	t <sub>f</sub>		130	180	
TOTAL GATE CHARGE $I_D = 12A$ ,	$Q_g$	55	-	120	nC
GATE TO SOURCE CHARGE V <sub>GS</sub> = 10V,	$Q_{gs}$	5	-	19	nC
GATE TO DRAIN CHARGE V <sub>DS</sub> =0.5xMax. Rating	$Q_gd$	25	-	70	nC
DIODE FORWARD VOLTAGE $T_C = 25^{\circ}C$ , $I_S = 12A$ ,	V <sub>SD</sub>			1.7	Volts
$V_{GS} = 0V$		-	-		
REVERSE RECOVERY CHARGE $T_J = 25^{\circ}C$ ,	Q <sub>RR</sub>			14	μС
$I_F = 12A$		-	-		•
$di/dt = 100A/\mu sec, V_{DD} = 50V$					
REVERSE RECOVERY TIME T <sub>J</sub> = 25°C,	t <sub>rr</sub>			1600	
$I_F = 12A$		-	-		nsec
$di/dt = 100A/\mu sec, V_{DD} = 50V$					
INPUT CAPACITANCE V <sub>GS</sub> = 0 V	Ciss		2700		
OUTPUT CAPACITANCE V <sub>DS</sub> = 25 V	Coss	-	600	-	pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	Crss		240		-

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## **MECHANICAL DIMENSIONS: in Inches / mm**



## SMD-1

### PINOUT TABLE

	PIN 1	PIN 2	PIN 3
N-CHANNEL MOSFET IN A SMD-1 PACKAGE	DRAIN	SOURCE	GATE

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